1. General description

The 74LVT374 is a high-performance product designed for V_{CC} operation at 3.3 V.

This device is an 8-bit, edge triggered register coupled to eight 3-state output buffers. The two sections of the device are controlled independently by the clock (pin CP) and output enable (pin \overline{OE}) control gates. The state of each Dn input (one setup time before the LOW-to-HIGH clock transition) is transferred to the corresponding flip-flops Qn output.

The 3-state output buffers are designed to drive heavily loaded 3-state buses, MOS memories, or MOS microprocessors.

The active LOW output enable (pin \overline{OE}) controls all eight 3-state buffers independent of the clock operation.

When pin \overline{OE} is LOW, the stored data appears at the outputs. When pin \overline{OE} is HIGH, the outputs are in the high-impedance OFF-state, which means they will neither drive nor load the bus.

2. Features and benefits

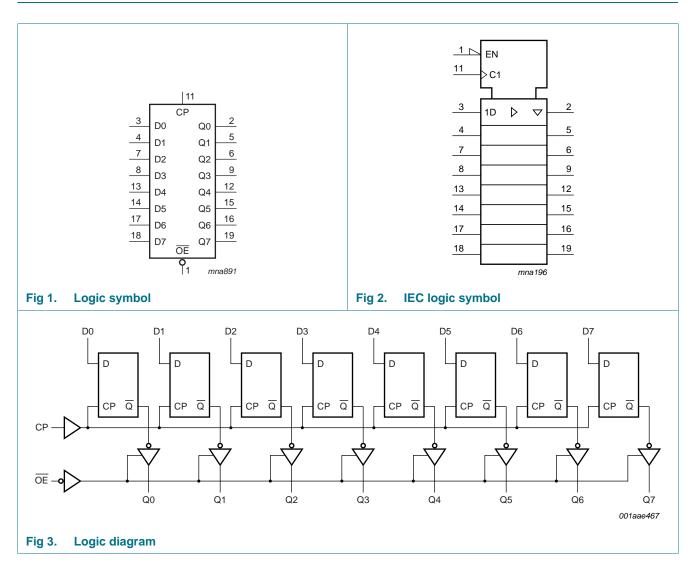
- Inputs and outputs arranged for easy interfacing to microprocessors
- 3-state outputs for bus interfacing
- Common output enable control
- TTL input and output switching levels
- Input and output interface capability to systems at 5 V supply
- Bus hold data inputs eliminate need for external pull-up resistors to hold unused inputs
- Live insertion and extraction permitted
- No bus current loading when output is tied to 5 V bus
- Power-up reset
- Power-up 3-state
- Latch-up protection
 - JESD78 class II exceeds 500 mA
- ESD protection:
 - HBM JESD22-A114E exceeds 2000 V
 - MM JESD22-A115-A exceeds 200 V
- Specified from –40 °C to +85 °C



3. Ordering information

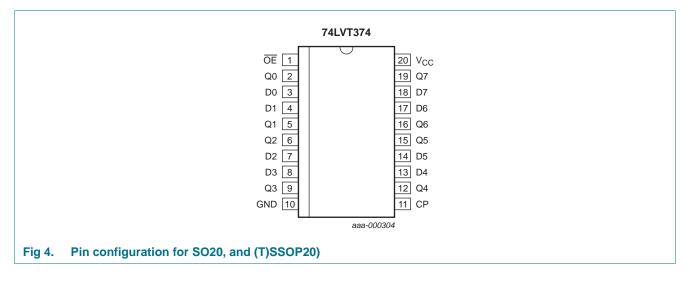
Table 1. Orde	ering information			
Type number	Package			
	Temperature range	Name	Description	Version
74LVT374D	–40 °C to +85 °C	SO20	plastic small outline package; 20 leads; body width 7.5 mm	SOT163-1
74LVT374DB	–40 °C to +85 °C	SSOP20	plastic shrink small outline package; 20 leads; body width 5.3 mm	SOT339-1
74LVT374PW	–40 °C to +85 °C	TSSOP20	plastic thin shrink small outline package; 20 leads; body width 4.4 mm	SOT360-1

4. Functional diagram



5. Pinning information

5.1 Pinning



5.2 Pin description

Table 2.	Pin description	
Symbol	Pin	Description
OE	1	output enable input (active LOW)
D0 to D7	3, 4, 7, 8, 13, 14, 17, 18	data input
GND	10	ground (0 V)
CP	11	clock pulse input (active rising edge)
Q0 to Q7	2, 5, 6, 9, 12, 15, 16, 19	data output
V _{CC}	20	supply voltage

6. Functional description

6.1 Function table

Table 3.Function table [1]

Operating mode	Control		Input	Internal registe	r Output
	OE	СР	Dn		Qn
Load and read register	L	\uparrow	I	L	L
			h	Н	Н
Hold	L	NC	Х	NC	NC
Disable outputs	Н	L or H	Х	NC	Z
		\uparrow	Dn	Dn	Z

[1] H = HIGH voltage level;

L = LOW voltage level;

 \uparrow = LOW-to-HIGH clock transition;

h = HIGH voltage level one setup time prior to the LOW-to-HIGH clock transition;

I = LOW voltage level one setup time prior to the LOW-to-HIGH clock transition;

Z = high-impedance OFF-state;

NC = no change;

X = don't care.

7. Limiting values

Table 4.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+4.6	V
VI	input voltage		<u>[1]</u> –0.5	+7.0	V
Vo	output voltage	output in OFF-state or HIGH-state	<u>[1]</u> –0.5	+7.0	V
I _{IK}	input clamping current	V _I < 0 V	-	-50	mA
Ι _{ΟΚ}	output clamping current	V _O < 0 V	-	-50	mA
lo	output current	output in LOW-state	-	128	mA
		output in HIGH-state	-	-64	mA
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		[2] _	150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 \ ^{\circ}C \ to \ +85 \ ^{\circ}C$	<u>[3]</u>	500	mW

[1] The input and output negative voltage ratings may be exceeded if the input and output clamp current ratings are observed.

[2] The performance capability of a high-performance integrated circuit in conjunction with its thermal environment can create junction temperatures which are detrimental to reliability.

[3] For SO20 packages: above 70 °C derate linearly with 8 mW/K.
 For SSOP20 and TSSOP20 packages: above 60 °C derate linearly with 5.5 mW/K.
 For DHVQFN20 packages: above 60 °C derate linearly with 4.5 mW/K.

8. Recommended operating conditions

Table 5.	Recommended operating conditions					
Symbol	Parameter	Conditions	Min	Max	Unit	
V _{CC}	supply voltage		2.7	3.6	V	
VI	input voltage		0	5.5	V	
V _{IH}	HIGH-level input voltage		2.0	-	V	
V _{IL}	LOW-level input voltage		-	0.8	V	
I _{OH}	HIGH-level output current		-	-32	mA	
I _{OL}	LOW-level output current		-	32	mA	
		current duty cycle ≤ 50 %; $f_i \geq 1~kHz$	-	64	mA	
T _{amb}	ambient temperature	in free air	-40	+85	°C	
$\Delta t / \Delta V$	input transition rise and fall rate	outputs enabled	-	10	ns/V	

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		T _{amb} =	–40 °C to +	85 °C	Unit
				Min	Typ <mark>[1]</mark>	Max	
V _{IK}	input clamping voltage	$V_{CC} = 2.7 \text{ V}; \text{ I}_{IK} = -18 \text{ mA}$		-1.2	-0.9	-	V
V _{ОН}	HIGH-level output voltage	V_{CC} = 2.7 V to 3.6 V; I_{OH} = $-100~\mu A$		$V_{CC} - 0.2$	$V_{CC}-0.1$	-	V
		V_{CC} = 2.7 V; I_{OH} = -8 mA		2.4	2.5	-	V
		V_{CC} = 3.0 V; I _{OH} = -32 mA		2.0	2.2	-	V
V _{OL}	LOW-level output voltage	V _{CC} = 2.7 V					
		I _{OL} = 100 μA		-	0.1	0.2	V
		I _{OL} = 24 mA		-	0.3	0.5	V
		V _{CC} = 3.0 V					
		I _{OL} = 16 mA		-	0.25	0.4	V
		I _{OL} = 32 mA		-	0.3	0.5	V
		$I_{OL} = 64 \text{ mA}$		-	0.4	0.55	V
V _{OL(pu)}	power-up LOW-level output voltage	V_{CC} = 3.6 V; I_{O} = 1 mA; V_{I} = GND or V_{CC}	[2]	-	0.13	0.55	V
I _I	input leakage current	all input pins; V_{CC} = 0 V or 3.6 V; V_{I} = 5.5 V		-	1	10	μA
		control pins; V_{CC} = 3.6 V; V_{I} = V_{CC} or GND		-	±0.1	±1	μA
		data pins; $V_{CC} = 3.6 V$	[3]				
		$V_I = V_{CC}$		-	0.1	1	μA
		$V_{I} = 0 V$		-5	-1	-	μA
I _{OFF}	power-off leakage current	$V_{CC} = 0$ V; V ₁ or V ₀ = 0 V to 4.5 V		-	1	±100	μA
ILO	output leakage current	V_{O} = 5.5 V and V_{CC} = 3.0 V; output HIGH	[4]	-	60	125	μA
BHL	bus hold LOW current	$V_{CC} = 3.0 \text{ V}; \text{ V}_{I} = 0.8 \text{ V}$		75	150	-	μA
I _{BHH}	bus hold HIGH current	$V_{CC} = 3.0 \text{ V}; \text{ V}_{I} = 2.0 \text{ V}$	[4]	-	-150	-75	μA
I _{BHHO}	bus hold HIGH overdrive current	$V_{CC} = 3.6; V_I = 0 V \text{ to } 3.6 V$	<u>[4]</u>	-	-	500	μA

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Symbol	Parameter	Conditions		T _{amb} =	Unit		
				Min	Typ <mark>[1]</mark>	Max	
I _{BHLO}	bus hold LOW overdrive current	$V_{CC} = 3.6; V_I = 0 V \text{ to } 3.6 V$		-500	-	-	μA
I _{O(pu/pd)}	power-up/power-down output current		<u>[5]</u>	-	1	±100	μΑ
I _{OZ}	OFF-state output current	V_{CC} = 3.6 V; V_I = V_{IH} or V_{IL}					
		output HIGH: V _O = 3.0 V		-	1	5	μΑ
		output LOW: $V_0 = 0.5 V$		-5	1	-	μΑ
I _{CC}	supply current	V_{CC} = 3.6 V; V_{I} = GND or $V_{CC};I_{O}$ = 0 A					
		outputs HIGH		-	0.13	0.19	mA
		outputs LOW		-	3	12	mA
		outputs disabled	[6]	-	0.13	0.19	mA
Δl _{CC}	additional supply current	per input pin; V _{CC} = 3 V to 3.6 V; one input at V _{CC} – 0.6 V and other inputs at V _{CC} or GND	[7]	-	0.1	0.2	mA
CI	input capacitance	V _I = 0 V or 3.0 V		-	4	-	pF
Co	output capacitance	outputs disabled; $V_0 = 0 V \text{ or } 3.0 V$		-	7	-	рF

Table 6. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

[1] Typical values are measured at V_{CC} = 3.3 V and T_{amb} = 25 °C.

[2] For valid test results, data must not be loaded into the flip-flops (or latches) after applying power.

[3] Unused pins at V_{CC} or GND.

[4] This is the bus hold overdrive current required to force the input to the opposite logic state.

[5] This parameter is valid for any V_{CC} between 0 V and 1.2 V with a transition time of up to 10 ms. From V_{CC} = 1.2 V to V_{CC} = 3.3 V \pm 0.3 V a transition time of 100 μ s is permitted. This parameter is valid for T_{amb} = 25 °C only.

[6] I_{CC} is measured with outputs pulled to V_{CC} or GND.

[7] This is the increase in supply current for each input at the specified voltage level other than V_{CC} or GND.

10. Dynamic characteristics

Table 7.Dynamic characteristics

Voltages are referenced to ground (GND = 0 V); for test circuit see Figure 9.

Symbol	Parameter	Conditions	Tan	_{nb} = -	-40 °C to	+85 °C	Unit
			Ν	lin	Typ <mark>[1]</mark>	Max	
t _{PLH}	LOW to HIGH propagation delay	CP to Qn; see <u>Table 6</u>					
	V_{CC} = 3.0 V to 3.6 V	1	.7	3.2	5.1	ns	
		$V_{CC} = 2.7 V$		-	-	5.8	ns
t _{PHL} HIGH to LOW propagation delay		CP to Qn; see Table 6					
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	2	.2	3.5	5.2	ns
		$V_{CC} = 2.7 V$		-	-	5.5	ns
t _{PZH}	OFF-state to HIGH propagation delay	OE to Qn; see Figure 6					
		V_{CC} = 3.0 V to 3.6 V	1	.5	3.2	5.3	ns
		$V_{CC} = 2.7 V$		-	-	7.3	ns

3.3 V octal D-type flip-flop; 3-state

Symbol	Parameter	Conditions		T _{amb} = -40 °C to -		+85 °C	Unit
				Min	Typ <mark>[1]</mark>	Max	
t _{PZL}	OFF-state to LOW propagation delay	OE to Qn; see Figure 7					
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$		2.0	3.4	5.2	ns
	$V_{CC} = 2.7 V$		-	-	6.1	ns	
t _{PHZ}	HIGH to OFF-state propagation delay	OE to Qn; see Figure 6					
		V_{CC} = 3.0 V to 3.6 V		1.9	4.3	6.7	ns
		$V_{CC} = 2.7 V$		-	-	7.1	ns
t _{PLZ}	LOW to OFF-state propagation delay	OE to Qn; see Figure 7					
		V_{CC} = 3.0 V to 3.6 V		2.0	3.4	5.1	ns
		$V_{CC} = 2.7 V$		-	-	5.1	ns
t _{su}	set-up time	Dn to CP; see Figure 8	[2]				
		V_{CC} = 3.0 V to 3.6 V		2.0	0.7	-	ns
		$V_{CC} = 2.7 V$		2.0	-	-	ns
t _h	hold time	Dn to CP; see Figure 8	[3]				
		V_{CC} = 3.0 V to 3.6 V		0.3	-0.5	-	ns
		$V_{CC} = 2.7 V$		0	-	-	ns
t _W	pulse width	CP input HIGH; see Figure 5	<u>[4]</u>				
		V_{CC} = 3.0 V to 3.6 V		1.5	0.8	-	ns
		$V_{CC} = 2.7 V$		1.5	-	-	ns
		CP input LOW; see Figure 5	<u>[4]</u>				
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$		2.5	1.7	-	ns
		V _{CC} = 2.7 V		3.0	-	-	ns
f _{max}	maximum frequency	CP input; see Figure 5					
		V_{CC} = 3.0 V to 3.6 V		125	200	-	MHz
		$V_{CC} = 2.7 V$		125	-	-	MHz

Table 7. Dynamic characteristics ... continued

[1] Typical values are at V_{CC} = 3.3 V and T_{amb} = 25 °C.

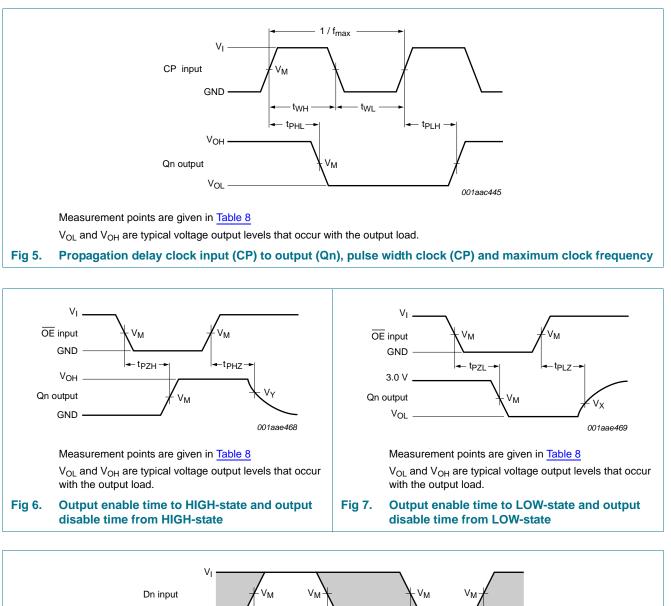
[2] t_{su} is the same as $t_{su(H)}$ and $t_{su(L)}$

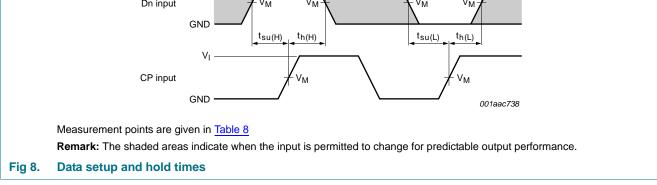
 $[3] \quad t_h \, \text{is the same as} \, t_{h(H)} \, \text{and} \, t_{h(L)}$

[4] t_W is the same as t_{WH} and t_{WL}

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11. Waveforms





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Table 8.	Measurement point	S		
Input		Output		
VM		V _M	V _X	V _Y
1.5 V		1.5 V	V _{OL} + 0.3 V	V _{OH} – 0.3 V

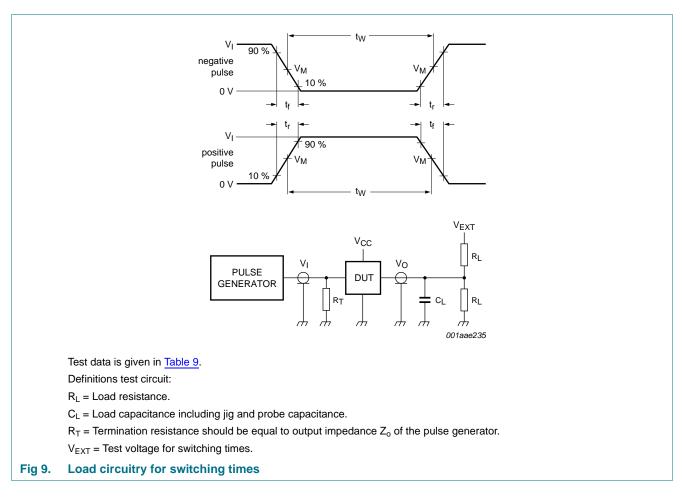


Table 9. Test data

Input		Load		V _{EXT}				
VI	f _i	t _W	t _r , t _f	CL	RL	t _{PHZ} , t _{PZH}	t _{PLZ} , t _{PZL}	t _{PLH} , t _{PHL}
2.7 V	\leq 10 MHz	500 ns	\leq 2.5 ns	50 pF	500 Ω	GND	6 V	open

3.3 V octal D-type flip-flop; 3-state

12. Package outline

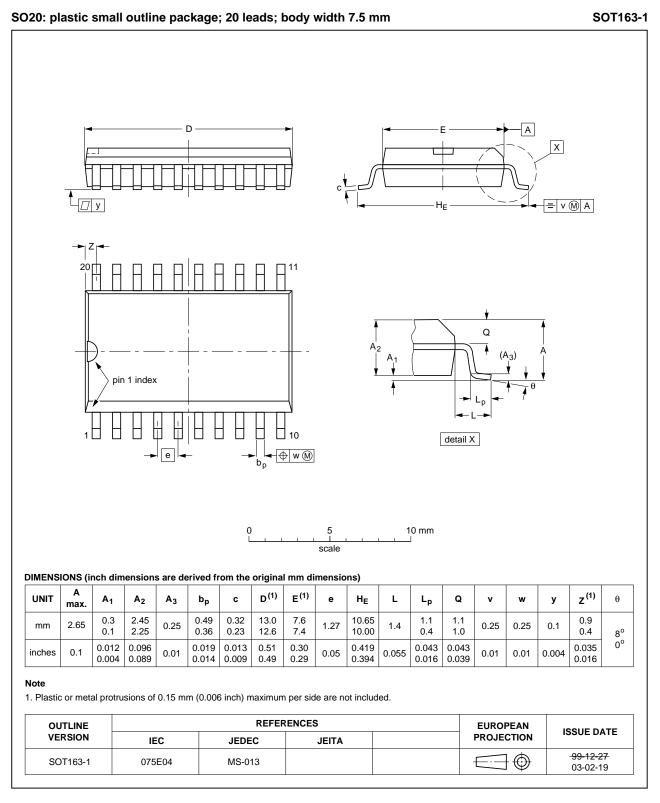


Fig 10. Package outline SOT163-1 (SO20)

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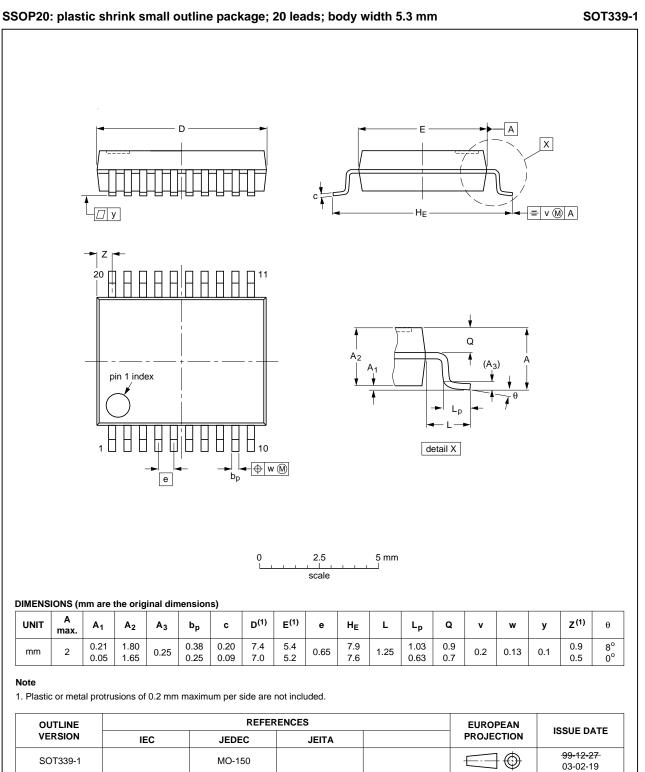


Fig 11. Package outline SOT339-1 (SSOP20)

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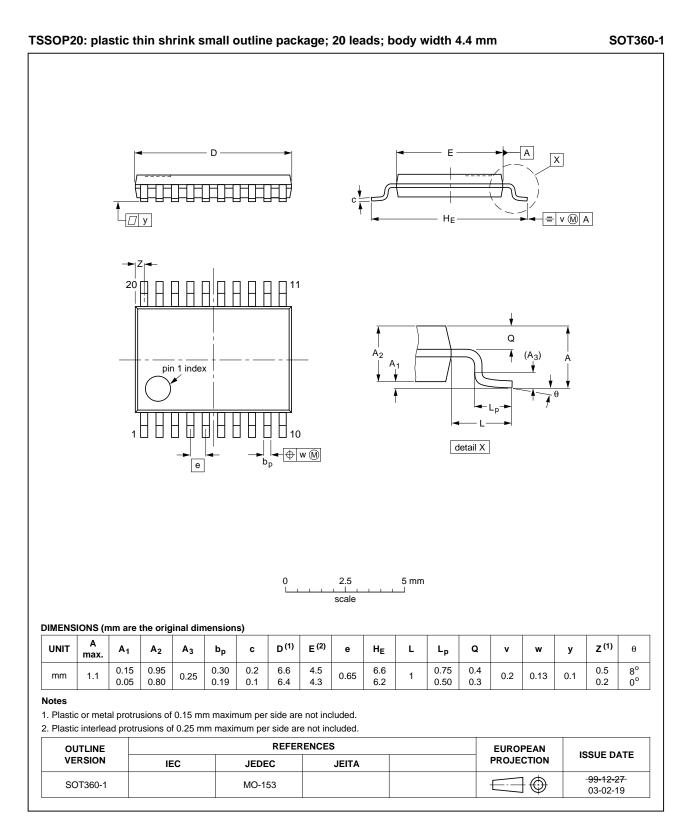


Fig 12. Package outline SOT360-1 (TSSOP20)

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13. Abbreviations

Table 10.	Abbreviations
Acronym	Description
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
MOS	Metal Oxide Semiconductor
TTL	Transistor-Transistor Logic

14. Revision history

Table 11. Revision	history			
Document ID	Release date	Data sheet status	Change notice	Supersedes
74LVT374 v.4	20111122	Product data sheet	-	74LVT374 v.3
Modifications:	 Legal pages 	s updated.		
74LVT374 v.3	20110914	Product data sheet	-	74LVT374 v.2
74LVT374 v.2	19980219	product specification	-	74LVT374 v.1
74LVT374 v.1	19960208	product specification	-	-

15. Legal information

15.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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3.3 V octal D-type flip-flop; 3-state

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